

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

TBC549
TBC550

PRIMARYLY INTENDED FOR LOW NOISE STAGE OF AUDIO AMPLIFIERS.

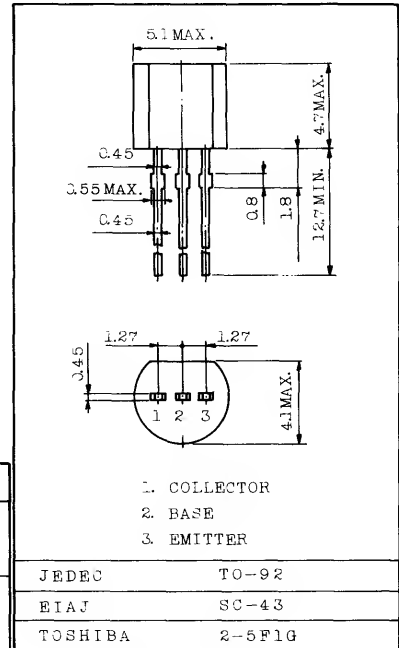
FEATURES:

- . Low Noise : 4dB Max. (TBC549)
3dB Max. (TBC550)
- . High V_{CEO} : 30V (TBC549)
45V (TBC550)
- . High h_{FE} : 200 ~ 800

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Breakdown Voltage	TBC549	V(BR)CBO	30	V
	TBC550		50	
Collector-Emitter Breakdown Voltage	TBC549	V(BR)CEO	30	V
	TBC550		45	
Emitter-Base Breakdown Voltage	V(BR)EBO	5	V	
Collector Current	DC	I_C	100	mA
	Peak	I_{CP}	200	
Base Current (Peak)	I_{BP}	200	mA	
Collector Power Dissipation	P_C	500	mW	
Junction Temperature	T_j	150	$^{\circ}C$	
Storage Temperature Range	T_{stg}	-65 ~ 150	$^{\circ}C$	

Unit in mm



Weight : 0.21g

TBC549

TBC550

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} =30V, I _E =0	-	-	15	nA
Emitter Cut-off Current		IEBO	VEB=5V, IC=0	-	-	1	μA
Collector-Emitter Breakdown Voltage	TBC549	V(BR)CEO	IC=1mA, IB=0	45	-	-	V
	TBC550			30	-	-	
DC Current Gain	TBC549-B TBC550-B	h _{FE}	V _{CE} =5V, IC=2mA	200	-	450	
	TBC549-C TBC550-C			420	-	800	
Small Signal Current Gain		h _{fe}	V _{CE} =5V, IC=2mA, f=1kHz	240	-	900	
Base-Emitter Voltage		V _{BE}	V _{CE} =5V, IC=2mA	580	660	700	mV
			V _{CE} =5V, IC=10mA	-	-	770	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	IC=10mA, IB=0.5mA	-	-	250	mV
			IC=100mA, IB=5mA	-	-	600	
Base-Emitter Saturation Voltage		V _{BE(sat)}	IC=10mA, IB=0.5mA	-	720	-	mV
			IC=100mA, IB=5mA	-	900	-	
Knee Voltage		V _{CEK}	IC=10mA, IB=Value for which IC=11mA, at V _{CE} =1V	-	400	600	mV
Transition Frequency		f _T	V _{CE} =5V, IC=10mA	-	300	-	MHz
Collector Output Capacitance		C _{ob}	V _{CB} =10V, f=1MHz	-	3.5	4.5	pF
Noise Figure	TBC549	NF	V _{CE} =5V, IC=0.2mA, R _g =2kΩ, f=30Hz ~ 15kHz	-	1.4	4	dB
	TBC550			-	1.4	3	
Noise Figure	TBC549	NF	V _{CE} =5V, IC=0.2mA R _g =2kΩ, f=1kHz	-	1	4	dB
	TBC550			-	1	4	
Equivalent Noise Voltage	TBC550	V _n	V _{CE} =5V, IC=0.2mA R _g =2kΩ, f=10 ~ 50Hz	-	-	0.135	μV